The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (Currently Amended) A semiconductor device comprising:
- a support which is a sheet comprising a ferromagnetic material including a magnetic sheet;
- a binding an adhesive material adjacent to the sheet comprising the ferromagnetic material the support including the magnetic sheet; [[and]]
- an element on an insulating film adjacent to the binding adhesive material[[,]]; and
 - a thin film transistor adjacent to the insulating film.
- 2. (Currently Amended) A semiconductor device according to claim 1, wherein the element is a thin film transistor, a light-emitting element having a layer containing an organic compound, the semiconductor device further comprises an element selected from group consisting of an element having liquid crystal, a memory element, a thin film diode, a photoelectric transducer comprising PIN junctions of silicon, or a silicon resistance element.
- 3. (Currently Amended) A semiconductor device according to claim 1 or claim 2, wherein the magnetic sheet comprising the ferromagnetic material is formed by mixing soft magnetic powder and synthetic resin, then and by magnetizing said mixture.
 - 4. (Currently Amended) A semiconductor device comprising:
 - a support which is a binding an adhesive material;
 - a protective film [[on]] over the binding material support;

an insulating film over the protective film; and

a middle processing component comprising a control section and an operation section, and a memory unit [[on an]] over the insulating film, adjacent to the binding material; and

wherein the middle processing component includes a thin film transistor of n-channel type and a thin film transistor of p-channel type.

5. (Previously Presented) A semiconductor device according to any one of claims 1, 2, or 4, wherein the semiconductor device is an authentication card, a video camera, a digital camera, a goggle type display, a car navigation system, a personal computer, or a mobile information terminal.

6.-16. (Canceled)

- 17. (New) A semiconductor device comprising:
- a support including a magnetic sheet;
- an adhesive material adjacent to the support including a magnetic sheet;
- an insulating film adjacent to the adhesive material; and
- a light emitting element adjacent to the insulating film,

wherein the light emitting element comprises a first electrode, a second electrode, and a light emitting layer.

- 18. (New) A semiconductor device comprising:
- a support including a magnetic sheet;
- an adhesive material over the support including a magnetic sheet;
- an insulating film over the adhesive material;
- a thin film transistor over the insulating film; and
- a light emitting element over the insulating film,

wherein the light emitting element comprises a first electrode, a second electrode, and a light emitting layer, and

wherein the first electrode is electrically connected to the thin film transistor.

- 19. (New) A semiconductor device comprising:
- an insulating film;
- a thin film transistor over the insulating film;
- a light emitting element over the insulating film;
- an adhesive material over the light emitting element; and
- a support including a magnetic sheet over the adhesive material,

wherein the light emitting element comprises a first electrode, a second electrode, and a light emitting layer, and

wherein the first electrode is electrically connected to the thin film transistor.

- 20. (New) A semiconductor device comprising:
- a first protective film;
- a thin film transistor over the first protective film;
- a support which is an adhesive material over the thin film transistor; and
- a second protective film over the support.
- 21. (New) An article comprising:
- a first support including magnetic material;
- a second support including a magnetic sheet adjacent to the first support;
- an adhesive material adjacent to the first support including a magnetic sheet;
- an insulating film adjacent to the adhesive material; and
- a thin film transistor adjacent to the insulating film.

- 22. (New) An article according to claim 21, wherein the first support is a steel plate.
- 23. (New) A semiconductor device according to claim 1, wherein the magnetic sheet comprises a material selected from the group consisting of barium ferrite, strontium ferrite, and rare earth magnet.
- 24. (New) A semiconductor device according to claim 17, wherein the magnetic sheet comprises a material selected from the group consisting of barium ferrite, strontium ferrite, and rare earth magnet.
- 25. (New) A semiconductor device according to claim 18, wherein the magnetic sheet comprises a material selected from the group consisting of barium ferrite, strontium ferrite, and rare earth magnet.
- 26. (New) A semiconductor device according to claim 19, wherein the magnetic sheet comprises a material selected from the group consisting of barium ferrite, strontium ferrite, and rare earth magnet.
- 27. (New) An article according to claim 21, wherein the magnetic sheet comprises a material selected from the group consisting of barium ferrite, strontium ferrite, and rare earth magnet.